

SK75GD126T

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SEMITOP® 4

IGBT Module

SK75GD126T

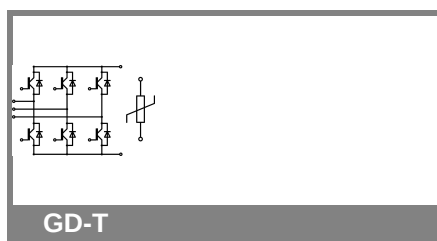
Target Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications

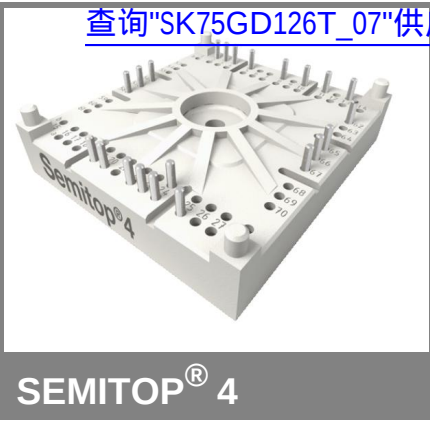
- Inverter up to 42 kVA
- Typ. motor power 18,5 kW



Absolute Maximum Ratings			$T_s = 25\text{ }^{\circ}\text{C}$, unless otherwise specified	
Symbol	Conditions		Values	Units
IGBT				
V_{CES}	$T_j = 25\text{ }^{\circ}\text{C}$		1200	V
I_C	$T_j = 150\text{ }^{\circ}\text{C}$	$T_s = 25\text{ }^{\circ}\text{C}$	88	A
		$T_s = 70\text{ }^{\circ}\text{C}$	67	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$		140	A
V_{GES}			± 20	V
t_{psc}	$V_{CC} = 600\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$ $V_{CES} < 1200\text{ V}$		10	μs
Inverse Diode				
I_F	$T_j = 150\text{ }^{\circ}\text{C}$	$T_s = 25\text{ }^{\circ}\text{C}$	91	A
		$T_s = 70\text{ }^{\circ}\text{C}$	68	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$		150	A
Module				
$I_{t(RMS)}$				A
T_{vj}			-40 ... +150	$^{\circ}\text{C}$
T_{stg}			-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.		2500	V

Characteristics			T _s = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 3 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}		T _j = 25 °C T _j = 125 °C			mA mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V		T _j = 25 °C T _j = 125 °C			nA nA
V _{CE0}			T _j = 25 °C T _j = 125 °C			V V
r _{CE}	V _{GE} = 15 V		T _j = 25°C T _j = 125°C			mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 75 A, V _{GE} = 15 V		T _j = 25°C _{chiplev.} T _j = 125°C _{chiplev.}			V V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V		f = 1 MHz			nF
C _{oes}						nF
C _{res}						nF
t _{d(on)}	R _{Gon} = 8,2 Ω di/dt = 1340 A/μs		V _{CC} = 600V I _{Cnom} = 75A			ns
t _r						ns
E _{on}						mJ
t _{d(off)}	R _{Goff} = 8,2 Ω di/dt = 1340 A/μs		T _j = 125 °C V _{GE} = -7/+15 V			ns
t _f						ns
E _{off}						mJ
R _{th(j-s)}	per IGBT					K/W

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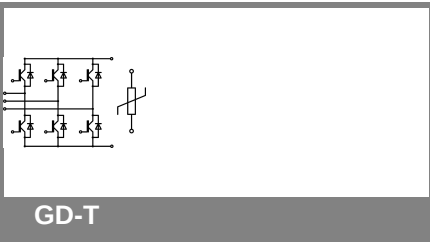
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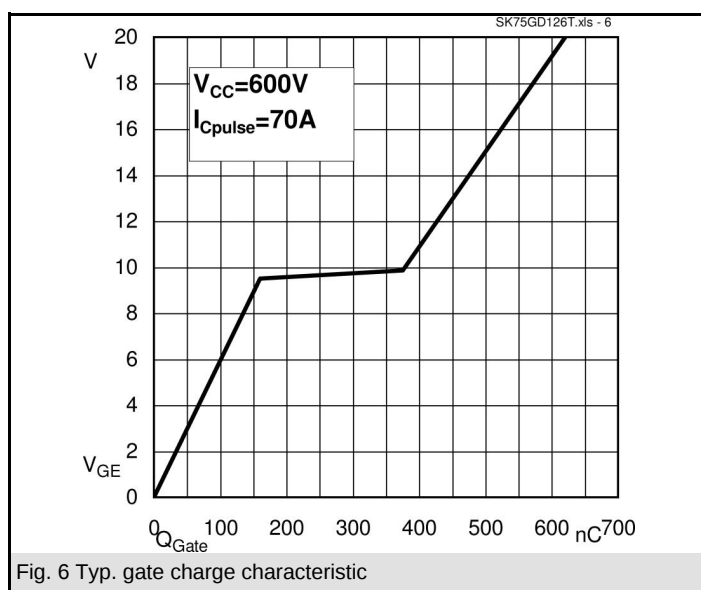
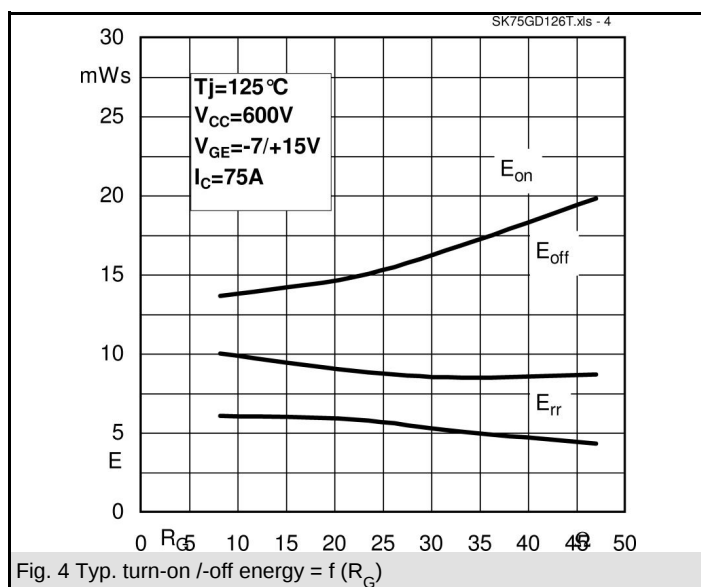
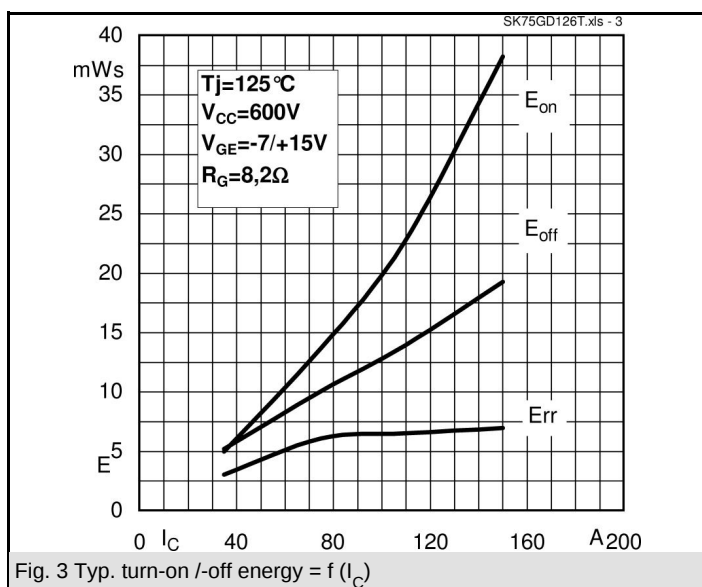
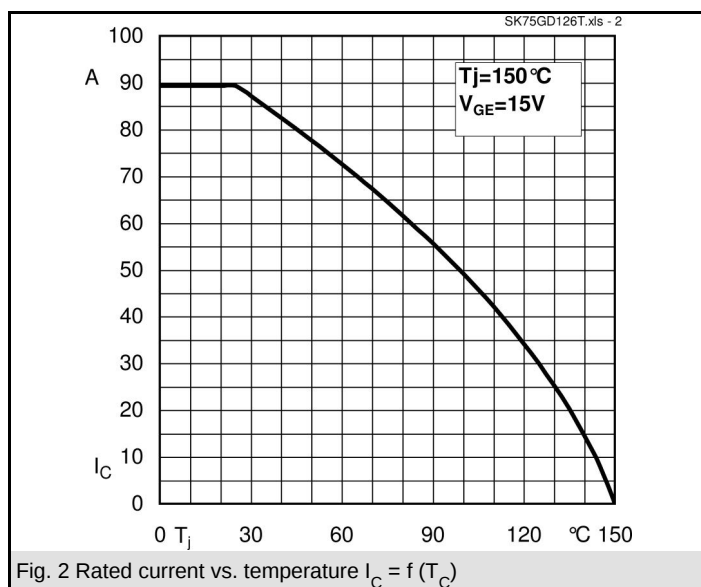
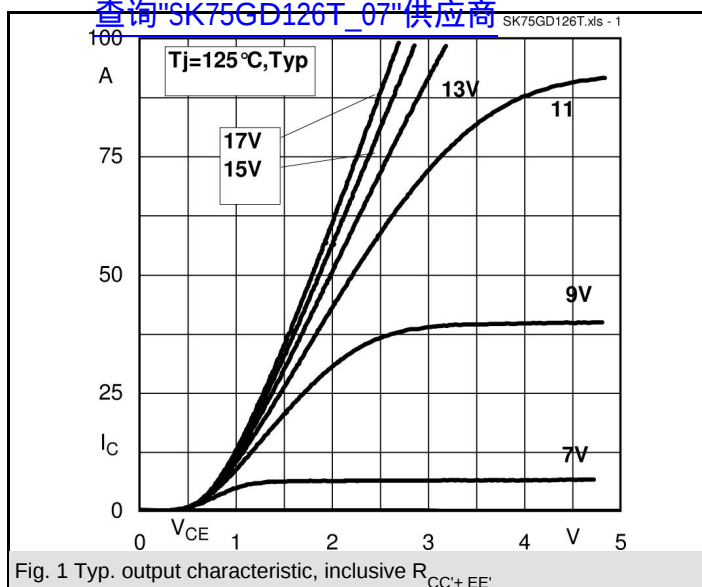


Characteristics						
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
V _F = V _{EC}	I _{Fnom} = 75 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,46		V
		T _j = 125 °C _{chiplev.}		1,4		V
V _{F0}		T _j = 25 °C		1,05		V
		T _j = 125 °C		0,95		V
r _F		T _j = 25 °C		5,5		mΩ
		T _j = 125 °C		6		mΩ
I _{RRM}	I _{Fnom} = 75 A di/dt = 1340 A/μs V _{CC} = 600V	T _j = 125 °C		70		A
Q _{rr}				20		μC
E _{rr}				6		mJ
R _{th(j-s)D}	per diode			0,7		K/W
M _s	to heat sink				3,5	Nm
w				60		g
Temperature sensor						
R ₁₀₀	T _s =100°C (R ₂₅ =5kΩ)			493±5%		Ω

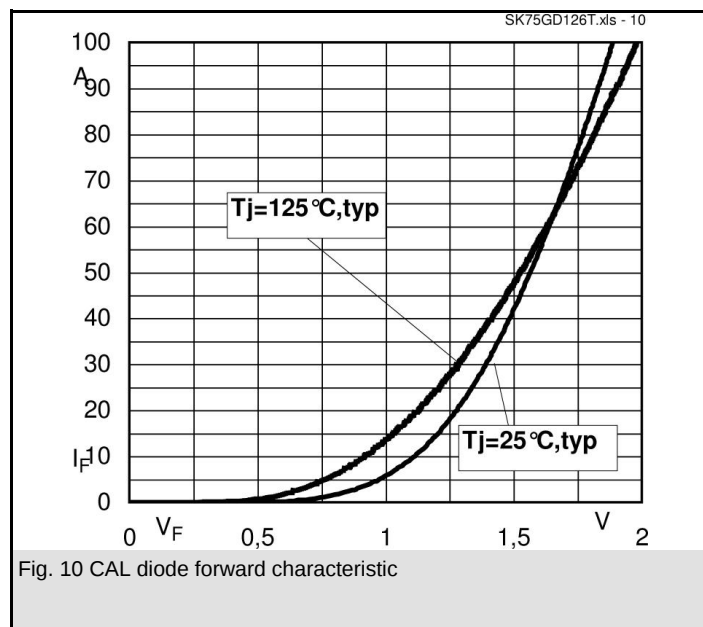
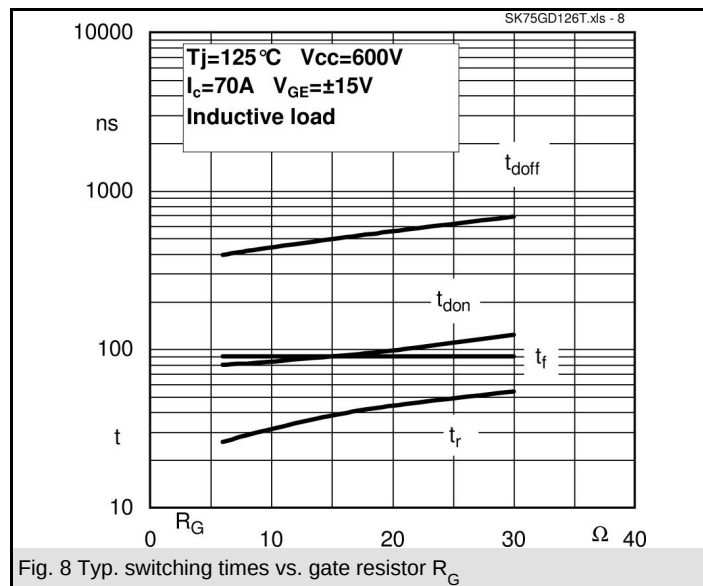
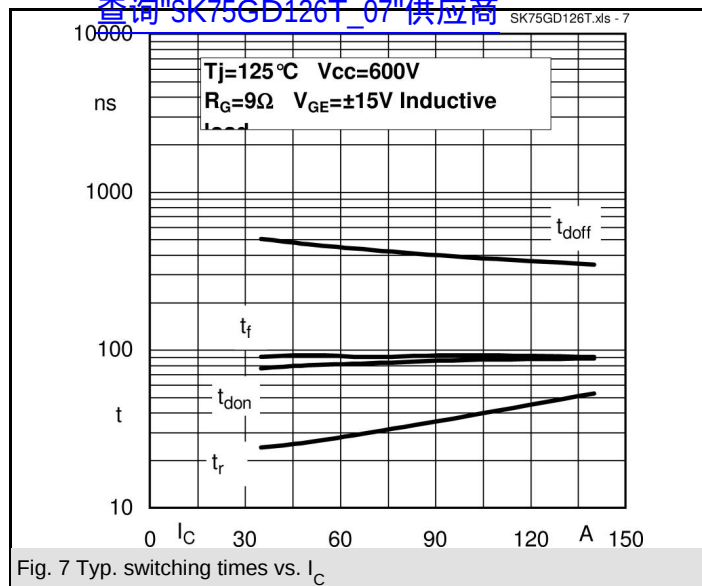
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

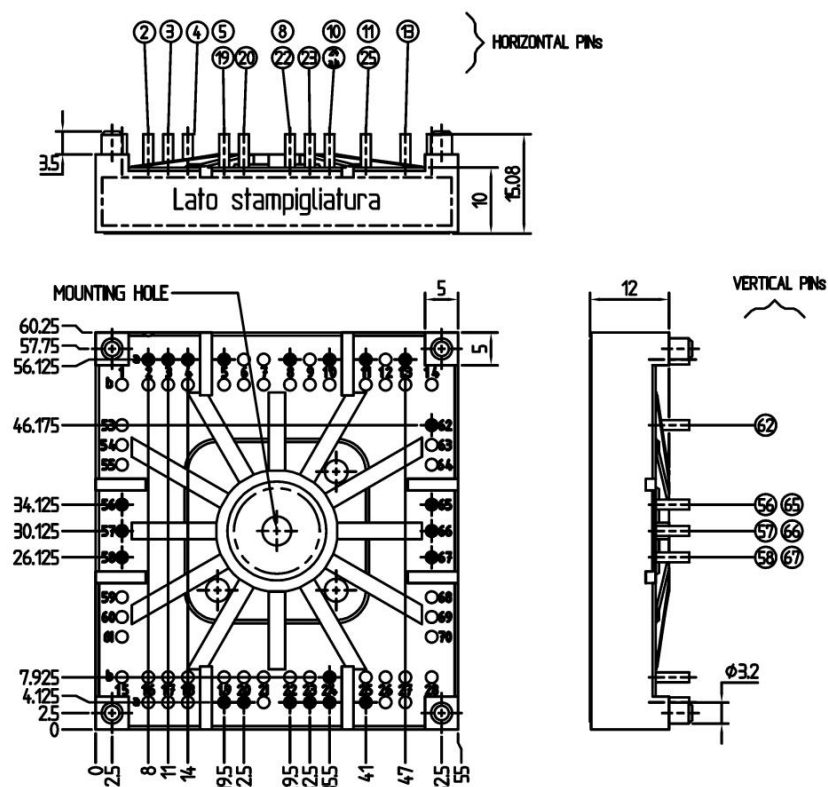
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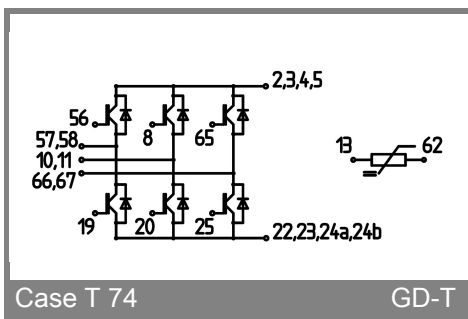


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Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



Case T 74

GD-T